

MMBT2222L, MMBT2222AL, SMMBT2222AL

General Purpose Transistors

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V_{CEO}	30 40	Vdc
Collector-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V_{CBO}	60 75	Vdc
Emitter-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V_{EBO}	5.0 6.0	Vdc
Collector Current - Continuous	I_C	600	mAdc
Collector Current - Peak (Note 3)	I_{CM}	1100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

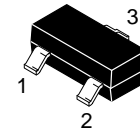
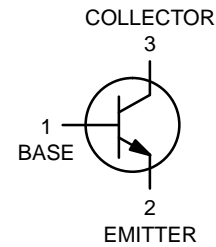
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Reference SOA curve.



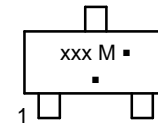
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SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



xxx = 1P or M1B
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 10 mA _{dc} , I _B = 0)	MMBT2222 MMBT2222A	V _{(BR)CEO}	30 40	– –	V _{dc}
Collector–Base Breakdown Voltage (I _C = 10 μA _{dc} , I _E = 0)	MMBT2222 MMBT2222A	V _{(BR)CBO}	60 75	– –	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	MMBT2222 MMBT2222A	V _{(BR)EBO}	5.0 6.0	– –	V _{dc}
Collector Cutoff Current (V _{CE} = 60 V _{dc} , V _{EB(off)} = 3.0 V _{dc})	MMBT2222A, SMMBT2222A	I _{CEX}	–	10	nA _{dc}
Collector Cutoff Current (V _{CB} = 50 V _{dc} , I _E = 0)	MMBT2222 MMBT2222A, SMMBT2222A	I _{CBO}	–	0.01	μA _{dc}
(V _{CB} = 60 V _{dc} , I _E = 0)	MMBT2222A, SMMBT2222A		–	0.01	
(V _{CB} = 50 V _{dc} , I _E = 0, T _A = 125°C)	MMBT2222		–	10	
(V _{CB} = 60 V _{dc} , I _E = 0, T _A = 125°C)	MMBT2222A, SMMBT2222A		–	10	
Emitter Cutoff Current (V _{EB} = 3.0 V _{dc} , I _C = 0)	MMBT2222A, SMMBT2222A	I _{EBO}	–	100	nA _{dc}
Base Cutoff Current (V _{CE} = 60 V _{dc} , V _{EB(off)} = 3.0 V _{dc})	MMBT2222A, SMMBT2222A	I _{BL}	–	20	nA _{dc}
ON CHARACTERISTICS					
DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , T _A = –55°C) (I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc}) (Note 4) (I _C = 150 mA _{dc} , V _{CE} = 1.0 V _{dc}) (Note 4) (I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc}) (Note 4)	MMBT2222A only MMBT2222 MMBT2222A, SMMBT2222A	h _{FE}	35 50 75 35 100 50 30 40	– – – – 300 – – –	–
Collector–Emitter Saturation Voltage (Note 4) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc})	MMBT2222 MMBT2222A, SMMBT2222A	V _{CE(sat)}	– –	0.4 0.3	V _{dc}
(I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	MMBT2222 MMBT2222A, SMMBT2222A		– –	1.6 1.0	
Base–Emitter Saturation Voltage (Note 4) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc})	MMBT2222 MMBT2222A, SMMBT2222A	V _{BE(sat)}	– 0.6	1.3 1.2	V _{dc}
(I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	MMBT2222 MMBT2222A, SMMBT2222A		– –	2.6 2.0	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (Note 5) (I _C = 20 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz)	MMBT2222 MMBT2222A, SMMBT2222A	f _T	250 300	– –	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)		C _{obo}	–	8.0	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	MMBT2222 MMBT2222A, SMMBT2222A	C _{ibo}	– –	30 25	pF
Input Impedance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{re}	– –	8.0 4.0	X 10 ^{–4}
Small–Signal Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h _{fe}	50 75	300 375	–

MMBT2222L, MMBT2222AL, SMMBT2222AL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant ($I_E = 20\text{ mAdc}$, $V_{CB} = 20\text{ Vdc}$, $f = 31.8\text{ MHz}$)	r_b, C_c	-	150	ps
Noise Figure ($I_C = 100\ \mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS (MMBT2222A only)

Delay Time	$(V_{CC} = 30\text{ Vdc}$, $V_{BE(\text{off})} = -0.5\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = 15\text{ mAdc}$)	t_d	-	10	ns
Rise Time		t_r	-	25	
Storage Time	$(V_{CC} = 30\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_s	-	225	ns
Fall Time		t_f	-	60	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
- f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

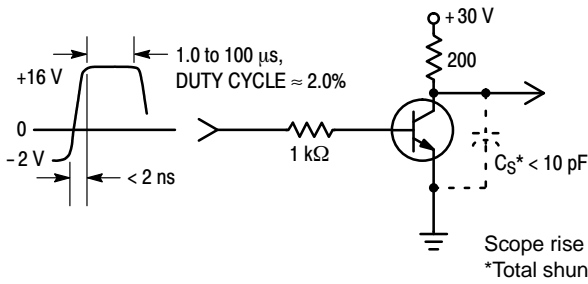


Figure 1. Turn-On Time

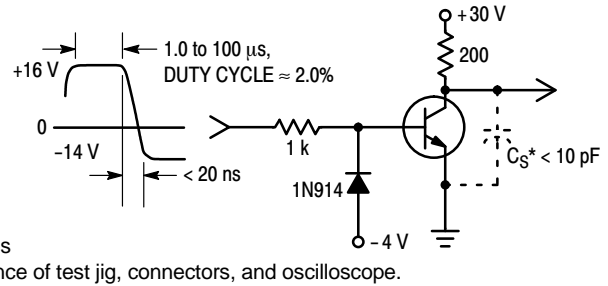


Figure 2. Turn-Off Time

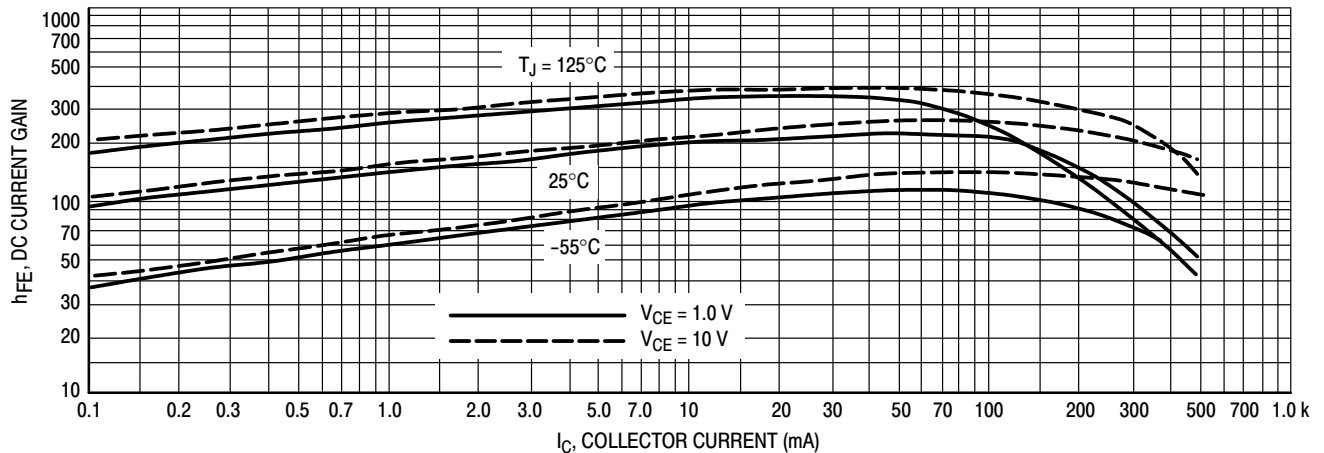


Figure 3. DC Current Gain

MMBT2222L, MMBT2222AL, SMMBT2222AL

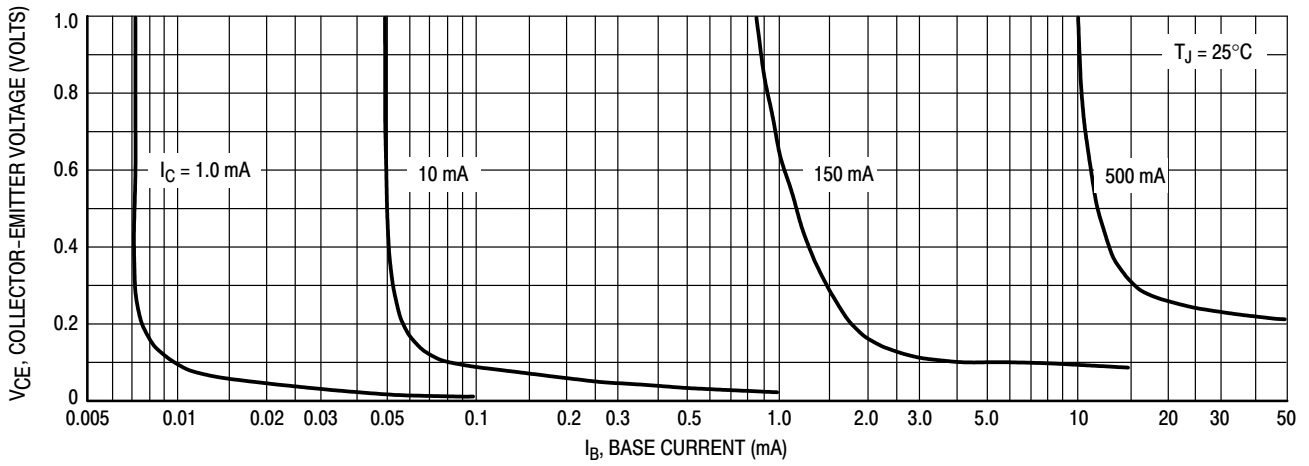


Figure 4. Collector Saturation Region

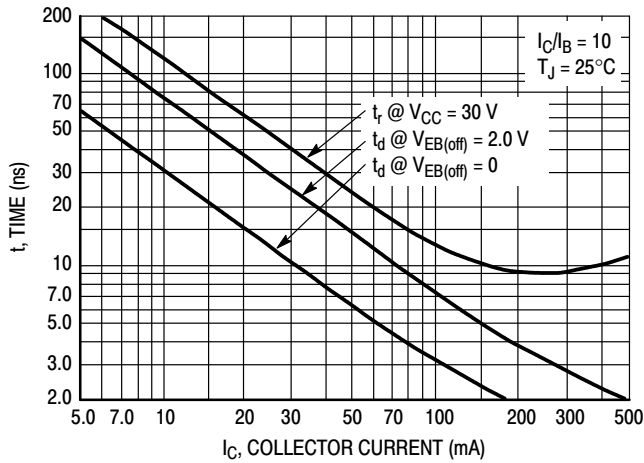


Figure 5. Turn-On Time

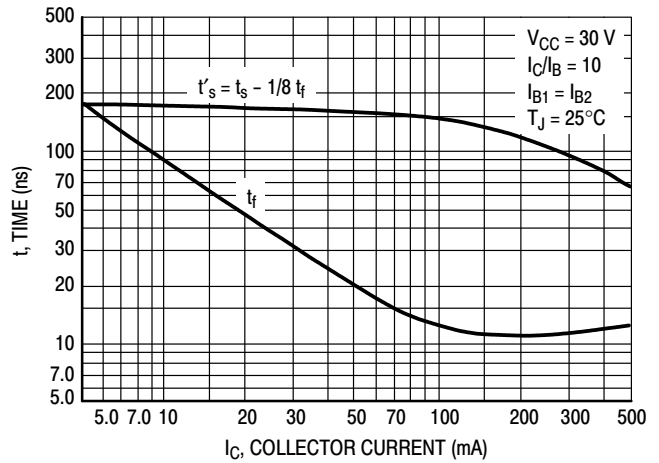


Figure 6. Turn-Off Time

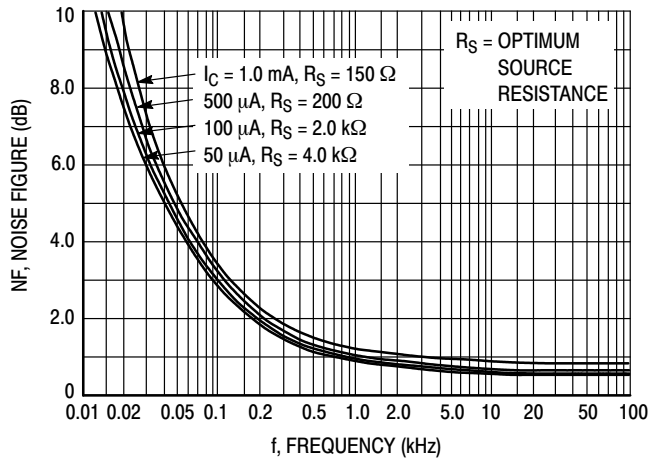


Figure 7. Frequency Effects

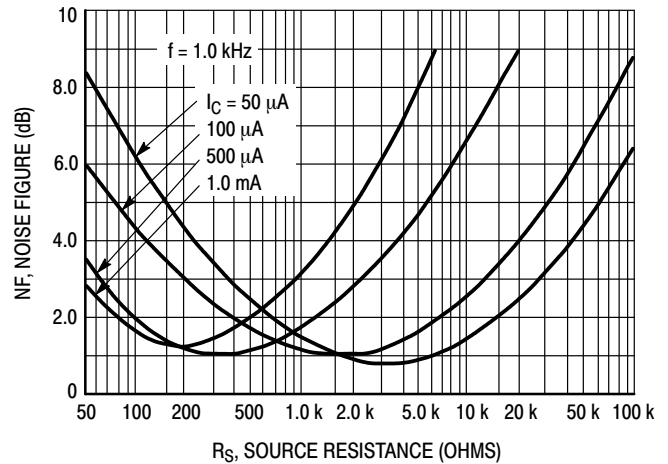


Figure 8. Source Resistance Effects

MMBT2222L, MMBT2222AL, SMMBT2222AL

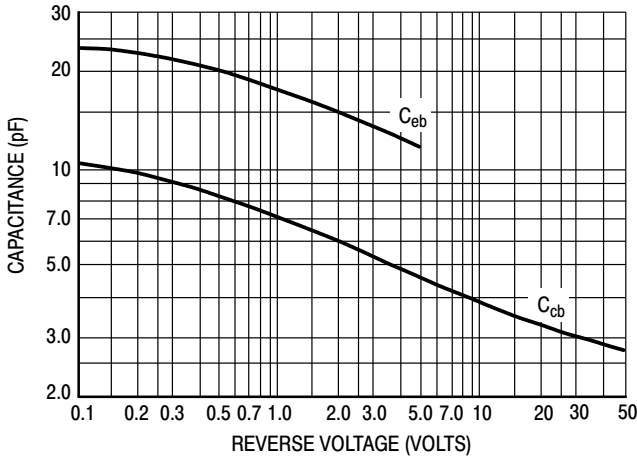


Figure 9. Capacitances

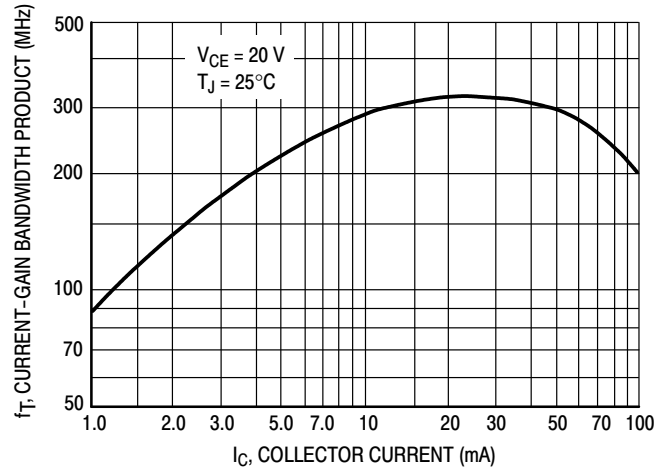


Figure 10. Current-Gain Bandwidth Product

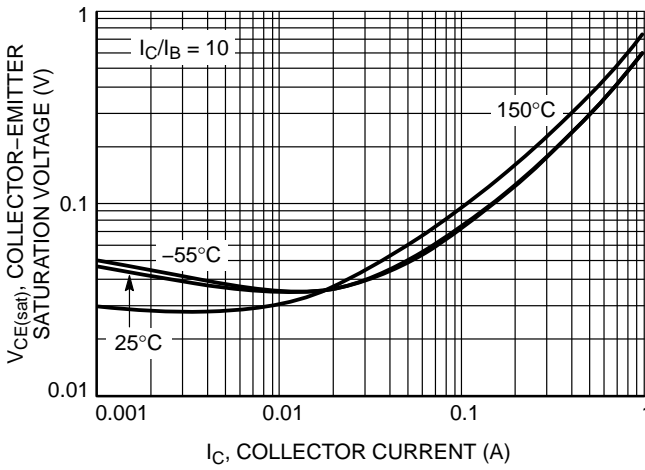


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

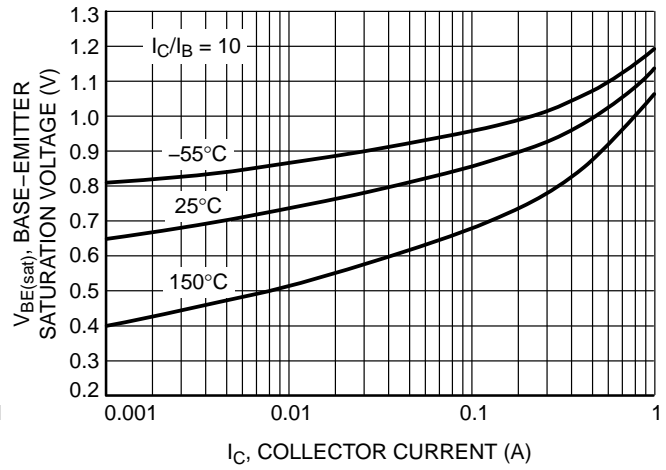


Figure 12. Base-Emitter Saturation Voltage vs. Collector Current

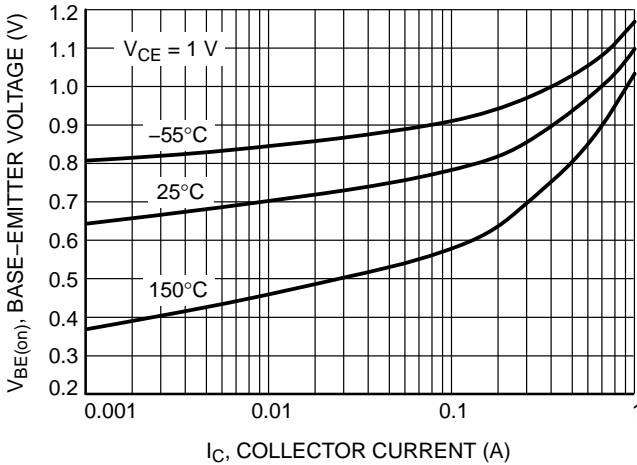


Figure 13. Base-Emitter Voltage vs. Collector Current

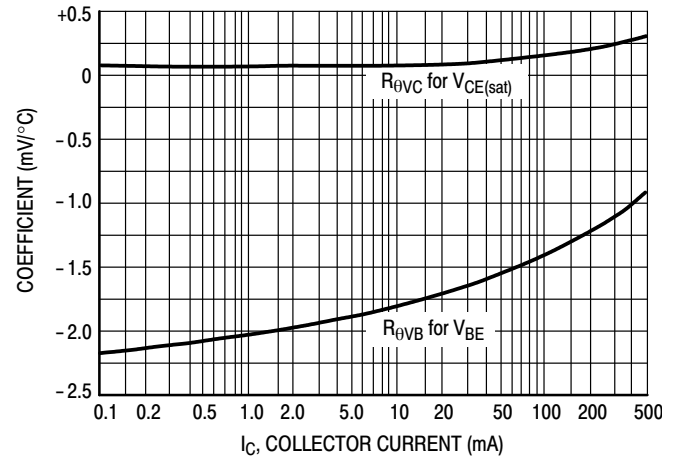
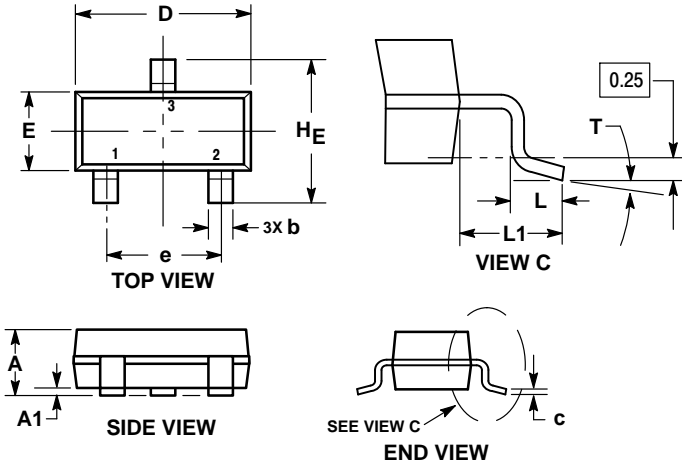


Figure 14. Temperature Coefficients

MMBT2222L, MMBT2222AL, SMMBT2222AL

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

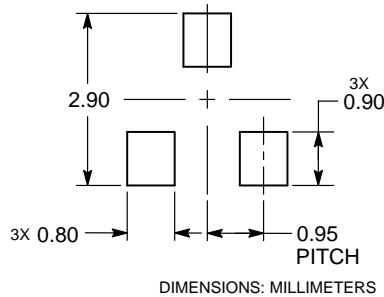
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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